

# *Falaphel INFN Project*

WP 2 Silicon Photonics

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INSTITUTE  
OF COMMUNICATION,  
INFORMATION  
AND PERCEPTION  
TECHNOLOGIES



Scuola Superiore  
Sant'Anna



# WP 2 Silicon Photonics

WP2 (Silicon Photonics) It will develop the SiPh building blocks including RM, MZM, bus waveguides, optical couplers and splitter, integrated thermal heaters. It will submit the MPW of a mini-block chip (2.5x~5 mm<sup>2</sup>). The fabricated mini-block will be characterised, providing information for the design and fabrication of the second full block chip (5x~5 mm<sup>2</sup>) that will be tested allowing the final integration with EIC.

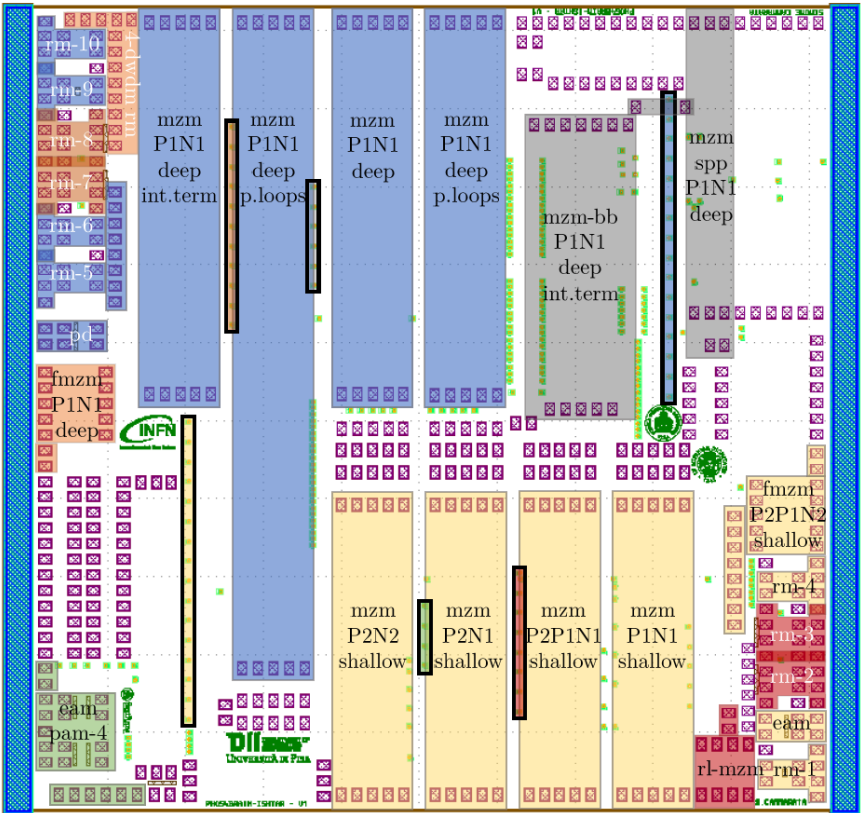
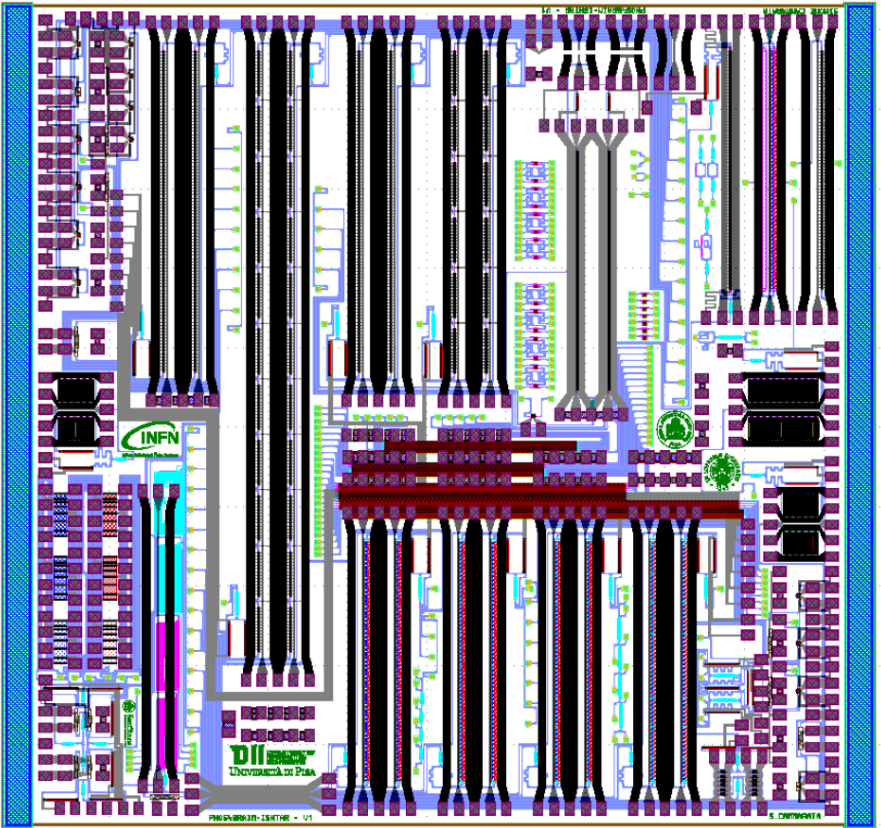
**D2.1 SiPh submissions for the MPW run of the first miniblock including the building blocks (SSSA, INFN PI, UNIFI, UNIMI) (T0+7)**

D2.2 SiPh submission for the MPW run full final block (SSSA, INFN PI, UNIFI, UNIMI) (T0+19)

D2.3 SiPh final PIC characterization (SSSA) (T0+31)

# Phos4Brain Chip

Final chip delivery postponed in August 2021



Tape Layout of the submitted design (June 2020)

# MPW run deadline 2021

SiPh submissions for the MPW run of the first miniblock  
2021 IMEC MPW run schedule

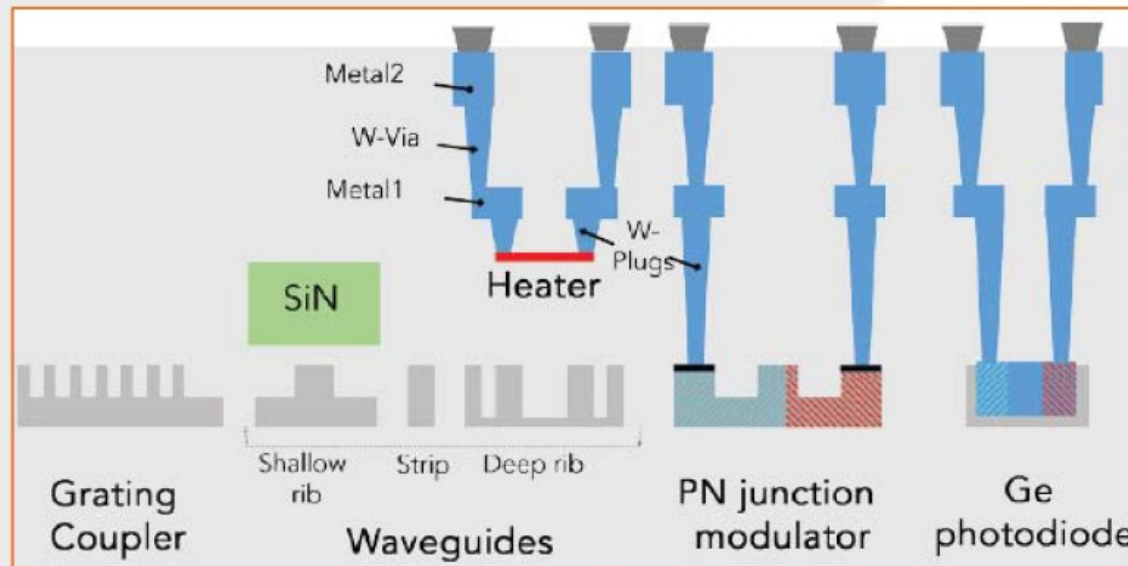
Half block 5.15mm x 2.5mm Price : 19 k€

imec

imec	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
imec Si-Photonics Passives+					12					13		
imec Si-Photonics iSiPP50G			10					25				
imec SiN-Photonics BioPIX 300					4							
imec GaN-IC on SOI 200V				21								
imec GaN-IC on SOI 650V	20									20		

# CEA/LETI Platform

Si310-PHMP2M Technology



200mm **SOI substrate** with  
**310nm Si** and  
2 $\mu$ m buried oxide  
6 implant levels for p-type and  
n-type for modulators and  
doped Si heaters

Cost with SiN Module 1500  
€/mm<sup>2</sup>

## Active components

High speed Photodetectors  
High speed Modulators

## Option

Optical edge coupler  
Under Bump Metallization  
Bumps &  $\mu$ -Bumps deposition

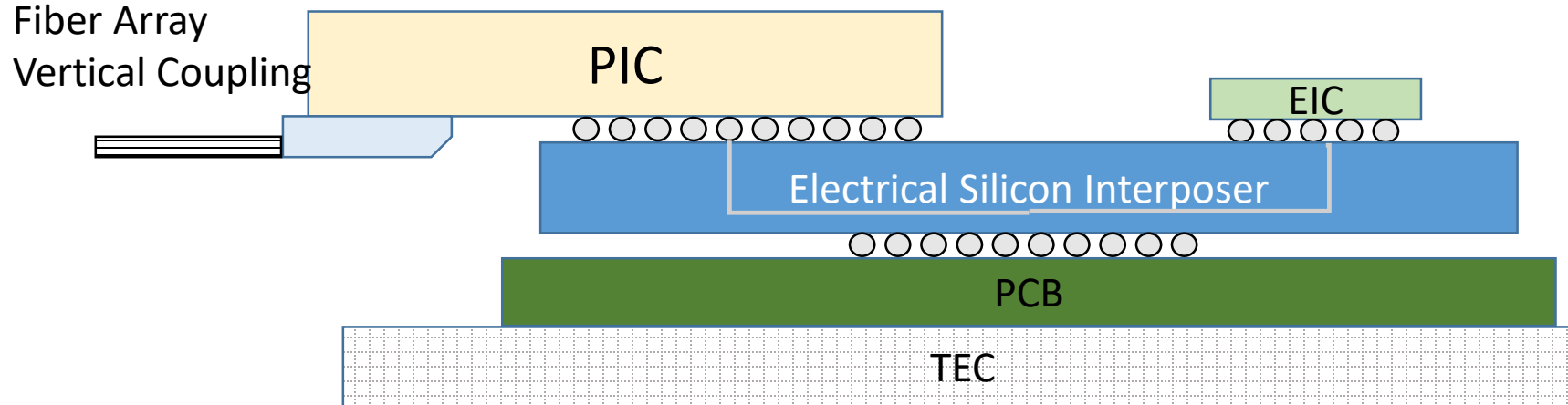
MPW Run deadline October 2021

# PIC/EIC Integration

Exploring possible solutions with the following technology centers

- Inphotec (2D Integration , 3D integration)
- Tyndall (2D and 3D integration)
- CEA –Leti (2.5 D integration through silicon interposer)

# PIC/EIC 2.5 Integration - Interposer



## PIC (1 chip)

Technology IMEC

Dimension (IMEC) 5x5 mm<sup>2</sup>

Evaluating other Technology: LETI (?)

Optical I/O max 16 Optical Fiber

Pitch fiber array 127 μm

Electrical Pad dimension

Pad 75x55 μm<sup>2</sup>

Pitch 100 μm

**Data rate 10-25Gbs**

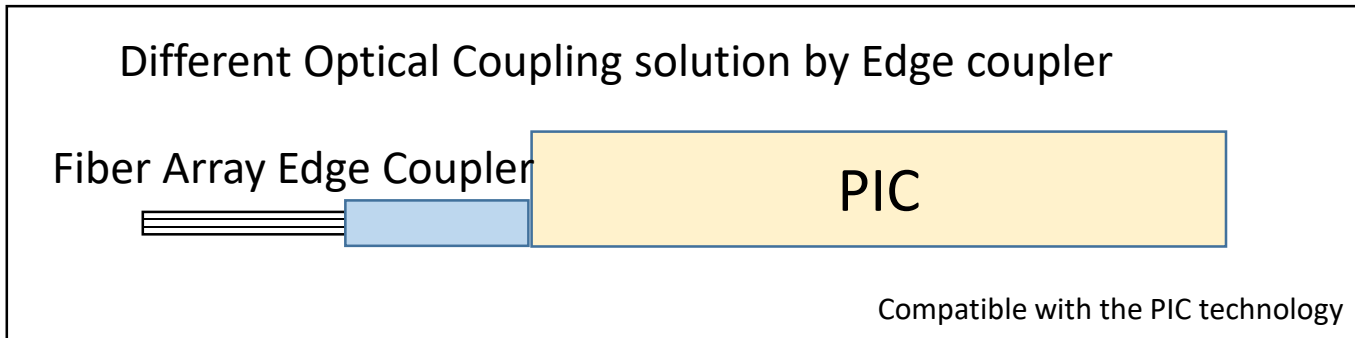
## EIC (4-5 Chip)

Technology 28 nm TSMC

Pitch 50-100 μm

Dimension 1 -2 mm<sup>2</sup>

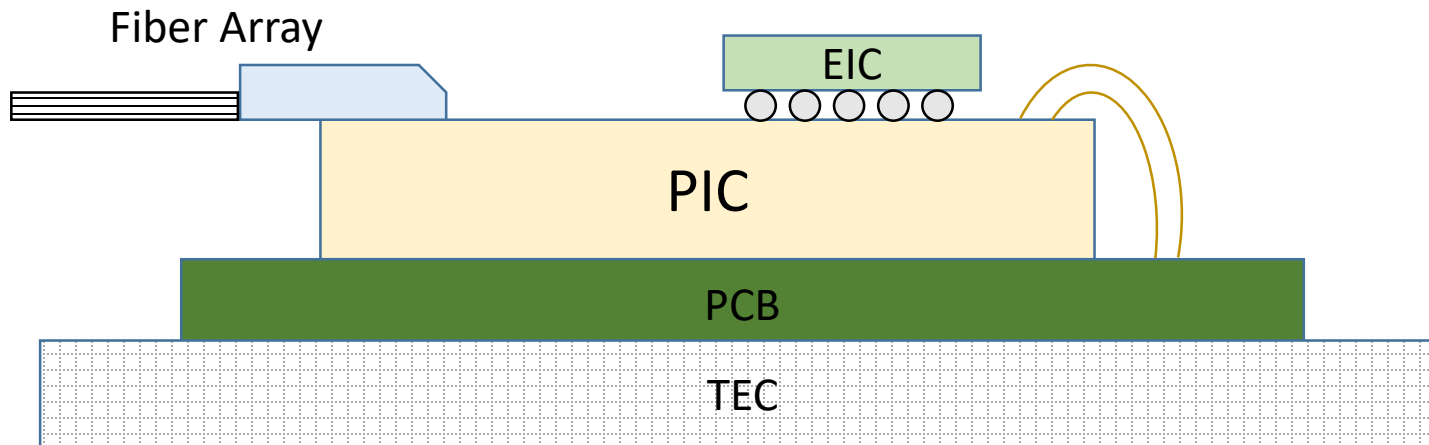
Thermal Issues to be taken into account



To be defined Bond Bump Material and packaging rules (Pitch, exclusions,.....)

Silicon Interposer for rad hard applications

# PIC/EIC 3D Integration



To be defined Bond Bump Material and packaging rules (Pitch, exclusions,.....)

## PIC (1 chip)

Technology IMEC

Dimension (IMEC)  $5 \times 5 \text{ mm}^2$

Evaluating other Technology: LETI (?)

Optical I/O max 16 Optical Fiber

Pitch fiber array  $127 \mu\text{m}$

Electrical Pad dimension

Pad  $75 \times 55 \mu\text{m}^2$

Pitch  $100 \mu\text{m}$

**Data rate 10-25Gbs**

## EIC (4-5 Chip)

Technology 28 nm TSMC

Pitch 50-100  $\mu\text{m}$

Dimension 1 -2  $\text{mm}^2$

Thermal Issues to be taken into account



# PIC/EIC 2D Integration

## PIC (1 chip)

Technology IMEC

Dimension (IMEC) 5x5 mm<sup>2</sup>

Evaluating other Technology: LETI (?)

Optical I/O max 16 Optical Fiber

Pitch fiber array 127 μm

Electrical Pad dimension

Pad 75x55 μm<sup>2</sup>

Pitch 100 μm

**Data rate 10-25Gbs**

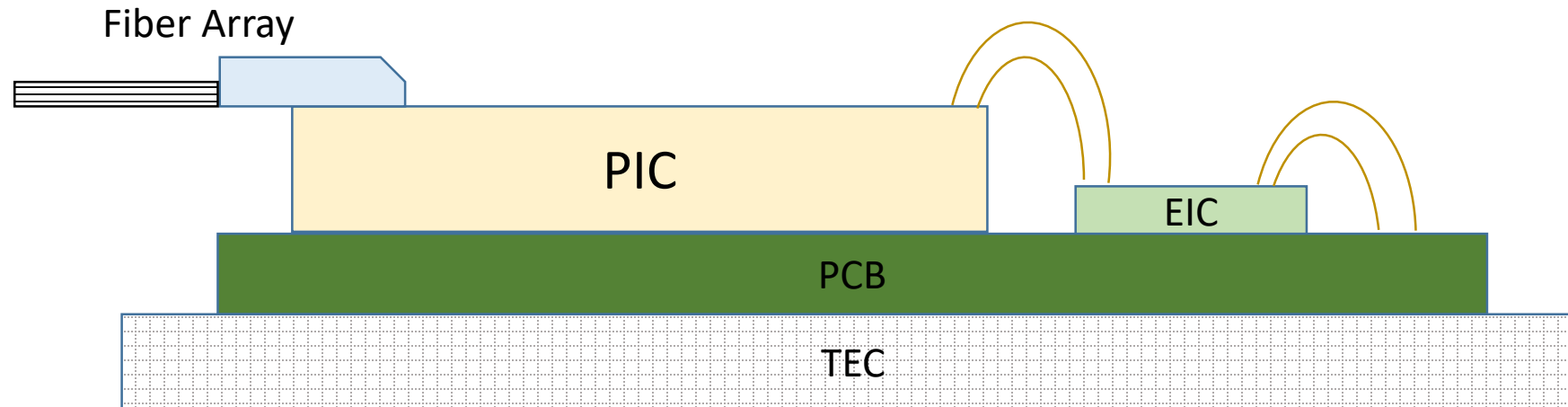
## EIC (4-5 Chip)

Technology 28 nm TSMC

Pitch 50-100 μm

Dimension 1 -2 mm<sup>2</sup>

Thermal Issues to be taken into account



To be defined Bond Bump Material and packaging rules (Pitch, exclusions,.....)

# AdR Recruitment

**Table 6.** Requested AdR. Type: Junior (J) / Senior (S)

AdR #	Type	Unit	Months	Research Topic
1	J	PI	30	PIC design and test. PIC-EIC integration and test
2	S	PI	24	Driver design. PIC-EIC integration and test
3	J	PI	18	PLL/CDR design and test
4	J	PV	30	DAC design and test
5	S	PV	24	FE design, test and integration in the demonstrator
6	J	PD	24	Irradiation tests and analysis

INFN Call n. 23192/2021 to award 1 grant for technological research:  
Topic: Design and test of integrated, radiation-tolerant photonic circuits for high-energy physics experiments

Deadline for the application 11<sup>th</sup> of June 2021